

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Continuous Reverse Voltage	$V_R$	50	V
Peak Repetitive Reverse Voltage	$V_{RRM}$	50	V
Continuous Forward Current	$I_F$	300	mA
Peak Repetitive Forward Current	$I_{FRM}$	600	mA
Forward Surge Current, $t_p=1\ \mu\text{s}$	$I_{FSM}$	4.0	A
Forward Surge Current, $t_p=1\ \text{s}$	$I_{FSM}$	1.0	A
Power Dissipation	$P_D$	500	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +200	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	350	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$BV_R$	$I_R=5.0\ \mu\text{A}$	75		V
$I_R$	$V_R=50\text{V}$		100	nA
$V_F$	$I_F=1.0\ \text{mA}$	0.54	0.62	V
$V_F$	$I_F=10\ \text{mA}$	0.66	0.74	V
$V_F$	$I_F=50\ \text{mA}$	0.76	0.86	V
$V_F$	$I_F=100\ \text{mA}$	0.82	0.92	V
$V_F$	$I_F=200\ \text{mA}$	0.87	1.0	V
$C_T$	$V_R=0, f=1.0\ \text{MHz}$		4.0	pF
$t_{rr}$	$I_R=I_F=10\ \text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\ \text{mA}$		4.0	ns

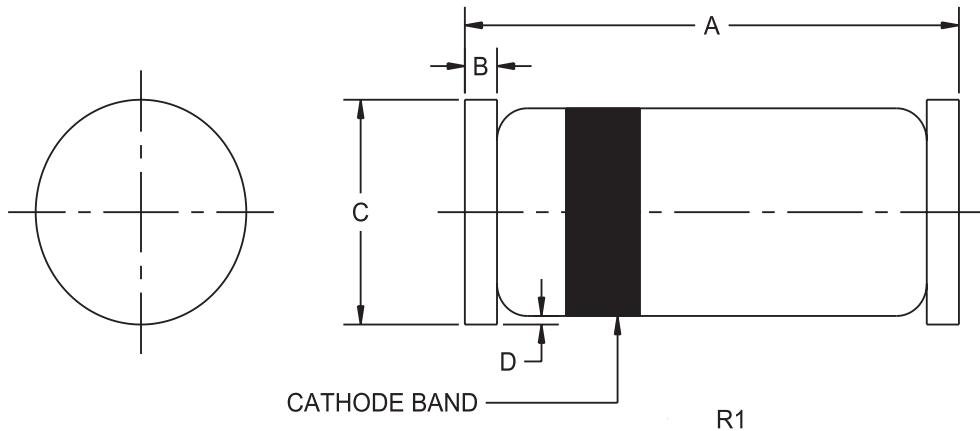
**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CLL4150 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in a hermetically sealed glass surface mount package, designed for high speed switching applications.

**MARKING CODE: CATHODE BAND.**

SOD-80 CASE - MECHANICAL OUTLINE



MARKING CODE: CATHODE BAND

SYMBOL	DIMENSIONS			
	INCHES	MILLIMETERS	MIN	MAX
A	0.130	0.146	3.30	3.71
B	0.016		0.41	
C (DIA)	0.051	0.067	1.30	1.70
D	-	0.004	-	0.10

SOD-80 (REV:R1)

R1 (26-September 2002)